

Title (en)

METHOD FOR FUNCTIONALLY TESTING MEMORY CELLS OF AN INTEGRATED SEMICONDUCTOR MEMORY

Title (de)

VERFAHREN ZUR FUNKTIONSÜBERPRÜFUNG VON SPEICHERZELLEN EINES INTEGRIERTEN HALBLEITERSPEICHERS

Title (fr)

PROCEDE POUR CONTROLER LE FONCTIONNEMENT DE CELLULES MEMOIRES D'UNE MEMOIRE A SEMICONDUCTEURS INTEGRES

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Application

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Abstract (en)

[origin: WO0046810A1] According to a method for functionally testing memory cells (MC) of an integrated semiconductor memory, a first group (1) of memory cells is tested. The test results (A, B) are copied at least three times and temporarily stored in a second group (2) of memory cells (MC), separately for each memory cell tested. The copies of each of the test results (A, B) are then compared and evaluated. The addresses of the respective memory cells of the second group (2) are determined by means of an address transformation (T) which is designed in such a way that significant clusters of functional errors in a defective second group (2) of memory cells (MC) do not affect the result of the test procedure.

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G11C 29/00

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Citation (search report)

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